# Supporting Information

# Band-like transport in non-fullerene acceptor semiconductor Y6

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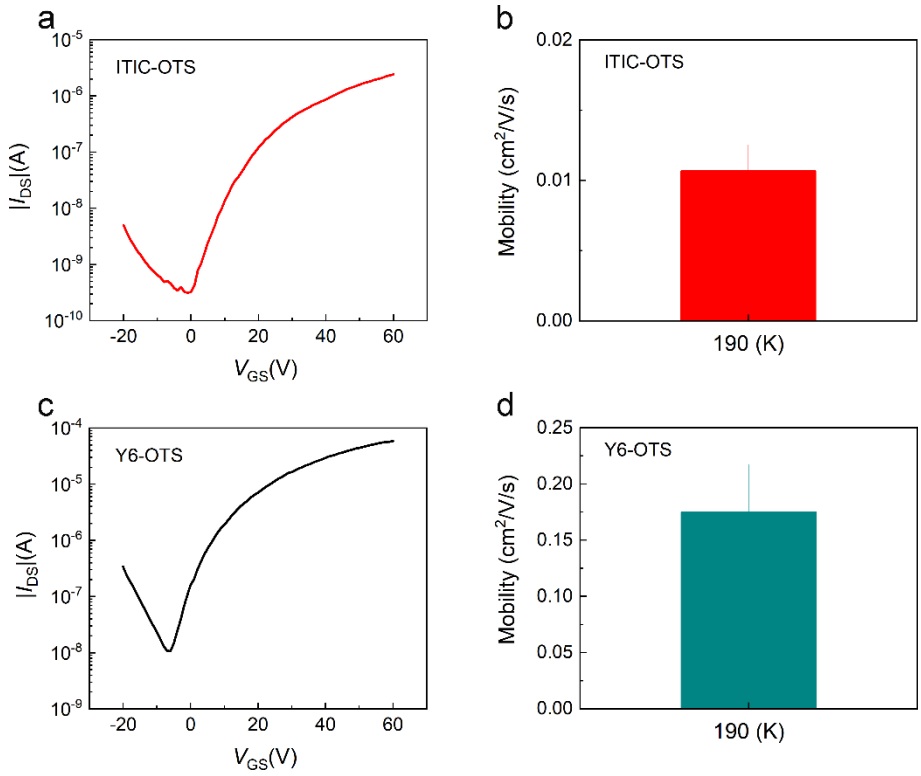


**Fig. S1 (a)** Transfer and **(b)** mobility of ITIC BGBC devices with OTS modified $SiO_2$. **(c)** Transfer and **(d)** mobility of Y6 BGBC devices with OTS modified $SiO_2$. The devices were annealed at temperature of 190 ℃.

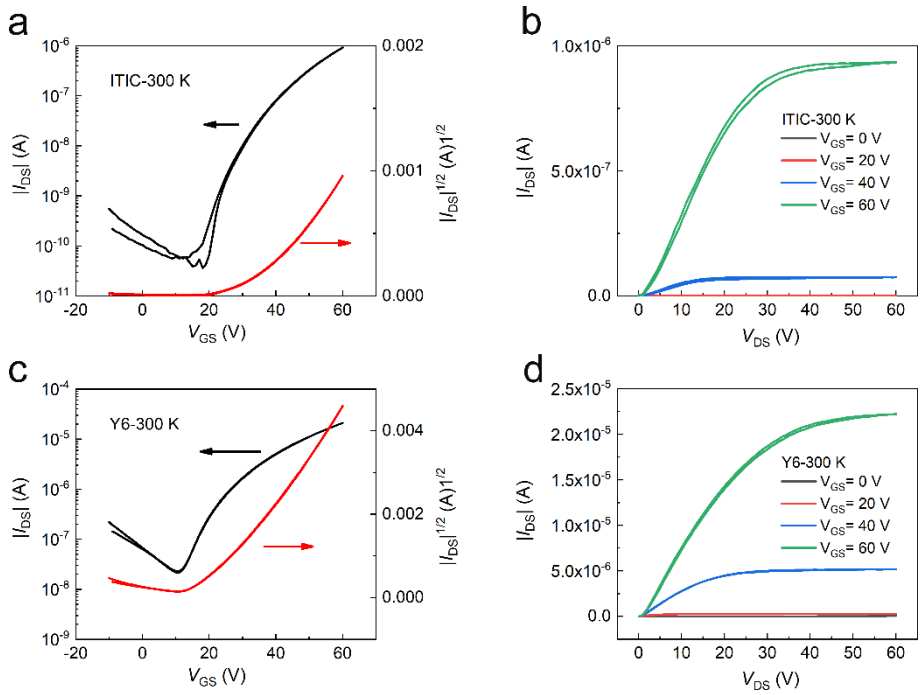


**Fig. S2 (a)** Transfer and **(b)** output characteristics of ITIC OTFTs (TGBC structure) at 300 K. **(c)** Transfer and **(d)** output characteristics of Y6 OTFTs (TGBC structure) at 300 K. The devices were annealed at temperature of 190 ℃.

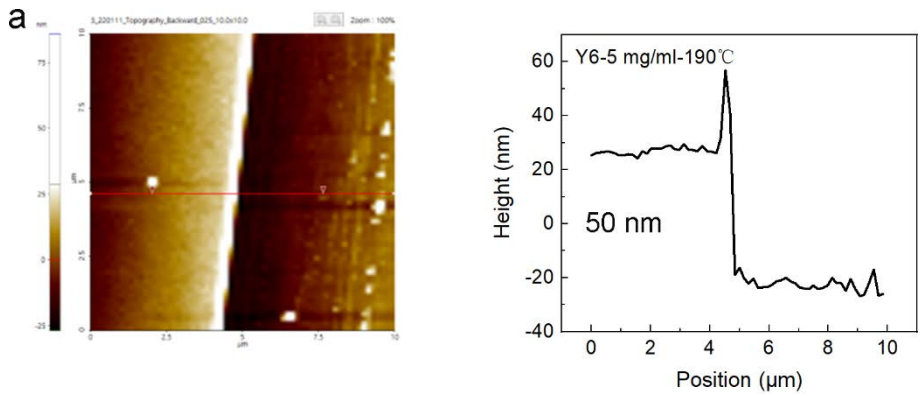


**Fig. S3.** AFM data showing the film thickness of Y6 films in the study.